

# LC5824, LC5823, LC5822

4-Bit Single-Chip Microcontrollers Featuring 4 KB to 8 KB of ROM, 1 Kbit of RAM, and an LCD Driver for Medium Speed Small-Scale Control Applications

# Overview

The LC5822, LC5823, and LC5824 are CMOS microcontrollers that feature the low-voltage operation required for battery-power applications and that provide 4 KB, 6 KB, or 8 KB of ROM, 1 kilobit of RAM, and an LCD driver.

These microcontrollers support an instruction set based on that of the earlier LC5800, LC5812, and LC5814 for excellent efficiency in software development.

# Applications

- LCD display in multi-function watches, timers, and other products
- Control and LCD display in timers
- Control and LCD display in miniature test equipment, health maintenance equipment, and other products
- These microcontrollers are optimal for products that include an LCD display, especially battery powered products.

Power options supply	Cycle times	Supply voltage range	Notes
EXT-V	10 µs	$V_{DD}$ = 2.3 to 3.6 V	When an 800-kHz ceramic oscillator is used
EXT-V	20 µs	$V_{DD}$ = 2.3 to 3.6 V	When an 400-kHz ceramic oscillator is used
EXT-V	61 µs	V <sub>DD</sub> = 2.3 to 3.6 V	When an 65-kHz crystal oscillator is used
EXT-V	122 µs	$V_{DD}$ = 2.0 to 3.6 V	When an 32-kHz crystal oscillator is used
Li	122 µs	V <sub>DD</sub> = 2.6 to 3.6 V*	When an 32-kHz crystal oscillator is used
Ag	122 µs	V <sub>DD</sub> = 1.3 to 1.65 V	When an 32-kHz crystal oscillator is used

Wide Allowable Operating Ranges

Note\*: When the backup flag is set, the BAK pin is connected to  $\mathsf{V}_{\mathsf{DD}}$ 

# **Features**

• These microcontrollers are high-end versions of the LC5800 and provide the following features.

Low Current Drain \* In halt mode (typical)

- Ceramic oscillator 400 kHz (3.0 V) 200 µA
- Crystal oscillator 32 kHz (1.5 V, Ag specifications)
   3.0 µA (LCD biases other than 1/3)
   4.5 µA (LCD drive: 1/3 bias)
- Crystal oscillator 32 kHz (3.0 V, Li specifications)
   2.0 µA (LCD biases other than 1/3) 6.0 µA (LCD drive: 1/3 bias)

Timer and Counter Functions

- One 8-bit programmable timer (May be used as an event counter)
- One 8-bit programmable reload timer
- Time base timer (for clocks)
- Watchdog timer
- 8-bit serial I/O (3-pin synchronous system)

Standby Functions

• Clock standby function (halt mode)

Only the oscillator circuits, the divider circuit, and the LCD driver operate. All other internal operations are stopped. This provides a power-saving function in which current drain is minimized, and allows a clock function to be implemented easily with low power dissipation.

Furthermore, low-speed and high-speed modes can be implemented by setting the operating modes of the two oscillator circuits.

- Full standby function (hold mode)
- Halt mode can be cleared by any of two external and two internal interrupts.
- Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.
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SANYO Electric Co., Ltd. Semiconductor Bussiness Headquarters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Improved I/O Functions

- External interrupt pins
- Input pins that can clear halt mode: 10 pins (maximum)
- Input ports with input resistors that can be controlled from software: 8 pins (maximum)
- Pins with a function that prevents the input port floating state: 8 pins (maximum)
- LCD drive pins: 4 pins (common), 42 pins (segment outputs)
- General-purpose I/O ports:

#### 16 pins (when all 4 P port pins are used)

- General-purpose inputs: 8 pins
- General-purpose outputs (1): 1 pin (the ALM pin)

• General-purpose outputs (2	):42 pins (when all 42 of the
	LCD segment outputs are
	switched over to function as
	general-purpose outputs)
• 8-bit serial output port:	1 set (3 pins: output, input,
	and clock)

Functional Overview

- Program ROM: 4096 × 16 bits LC5824 3072 × 16 bits LC5823 2048 × 16 bits LC5822
- Internal RAM:  $256 \times 4$  bits
- All instructions execute in a single cycle.
- Extensive set of interrupt functions for clearing halt and hold mode
  - 8 halt mode clearing functions
  - 5 hold mode clearing functions
  - 6 interrupt functions
  - Subroutines can be nested up to 8 levels (Specialpurpose registers that are shared with the interrupt function are built in.)
- · Powerful hardware to increase system processing capacity
  - Segment port related hardware
    - Built-in segment PLA circuit
    - Built-in segment decoder
    - Support for six different LCD drive specifications Outputs can be switched to CMOS levels
  - Built-in 8-bit synchronous serial I/O circuit
  - 8-bit read/write timer (plus a separate 8-bit prescaler; can be used as and event counter)
  - 8-bit reload timer (plus built-in 8-bit prescaler)
  - Built-in 8-bit prescaler (for use with timer 1, timer 2, and the serial counter)
  - All of RAM can be used a working area (RAM bank system)
  - Dedicated data pointer register for RAM access
  - 15-stage divider circuit for clocks (also used as the LCD voltage alternation frequency generator)
  - 8-bit table reference function (reads 8-bit ROM data)
  - Chattering prevention circuit (on two ports)
  - Alarm signal generation circuit

• LCD panel drive output pins with high flexibility (42 pins)

Drive system	Number of driven segments	Required number of common pins
bias · duty	168 segments	4 pins
bias · duty	126 segments	3 pins
bias · duty	168 segments	4 pins
bias · duty	126 segments	3 pins
bias · duty	84 segments	2 pins
Static drive	42 segments	1 pin

 The LCD output pins can be switched to function as general-purpose outputs.

CMOS/p-channel/n-channel type combinations: Up to 42 pins

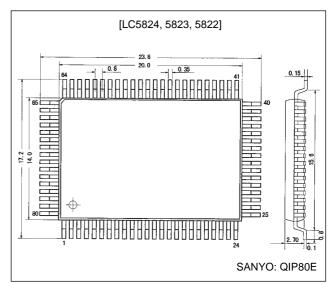
- An alternation frequency appropriate for the LCD panel used can be selected.
- An oscillator appropriate for your system's specifications can be selected.
  - A 32- or 65-kHz crystal oscillator can be selected (Used when a clock function is required or for low current drain operation.)
  - A ceramic oscillator with a frequency from 400 kHz to 2 MHz can be selected (when high-speed operation is required.)

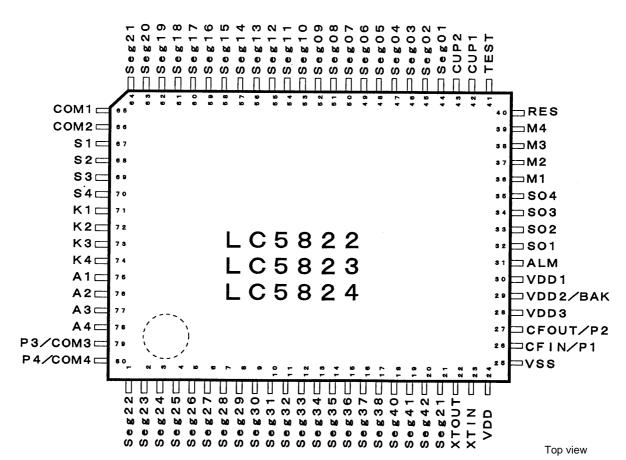
Available delivery formats: QIP-80 and chip

# **Package Dimensions**

#### unit: mm

#### 3174-QFP80E

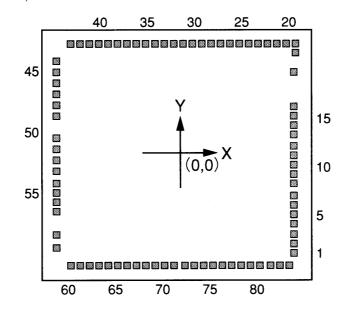




#### **Pin Assignment**

#### **Pad Arrangement**

Chip size: 4.92 mm  $\times$  5.15 mm Pad size: 120  $\mu m$   $\times$  120  $\mu m$  Chip thickness 480  $\mu m$  (chip specifications)



#### **Pad Coordinates**

	D.	Coordi	nates		5.	Coordi	nates		Ċ.	Coordi	nates
PAD No.	Pin	Χμm	Υμm	PAD No.	Pin	Χμm	Υμm	PAD No.	Pin	Χμm	Υµm
60	Seg 22	-2030	-2178	5	V <sub>DD</sub> 3	2257	-1212	33	Seg 11	-194	2178
61	Seg 23	-1850	-2178	6	V <sub>DD</sub> 2/BAK	2257	-1032	34	Seg 12	-374	2178
62	Seg 24	-1670	-2178	7	V <sub>DD</sub> 1	2257	-852	35	Seg 13	-546	2178
63	Seg 25	-1490	-2178	8	ALM	2257	-601	36	Seg 14	-726	2178
64	Seg 26	-1310	-2178	9	SO1	2257	-419	37	Seg 15	-906	2178
65	Seg 27	-1130	-2178	10	SO2 I/O port	2257	-236	38	Seg 16	-1086	2178
66	Seg 28	-950	-2178	11	SO3 I/O port	2257	56	39	Seg 17	-1266	2178
67	Seg 29	-770	-2178	12	SO4 I/O port	2257	132	40	Seg 18	-1446	2178
68	Seg 30	-590	-2178	13	M1	2257	364	41	Seg 19	-1626	2178
69	Seg 31	-410	-2178	14	M2 I/O port	2257	544	42	Seg 20	-1806	2178
70	Seg 32	-230	-2178	15	M3 I/O port	2257	724	43	Seg 21	-1986	2178
71	Seg 33	-50	-2178	16	M4 I/O port	2257	904	44	COM1	-2270	1871
72	Seg 34	122	-2178	17	RES I/O port	2257	1636	45	COM2	-2270	1628
73	Seg 35	302	-2178	18	Test	2330	1998	46	S1	-2270	1367
74	Seg 36	482	-2178	19	Test	2330	2178	47	S2 Input port	-2270	1140
75	Seg 37	662	-2178	20	TST	2150	2178	48	S3 Input port	-2270	960
76	Seg 38	842	-2178	21	CUP1	1970	2178	49	S4 Input port	-2270	734
77	Seg 39	1022	-2178	22	CUP2	1790	2178	50	K1	-2270	328
78	Seg 40	1202	-2178	23	Seg 1	1606	2178	51	K2 Input port	-2270	88
79	Seg 41	1382	-2178	24	Seg 2	1426	2178	52	K3 Input port	-2270	-140
80	Seg 42	1562	-2178	25	Seg 3	1246	2178	53	K4 Input port	-2270	-380
81	XC	1774	-2178	26	Seg 4	1066	2178	54	A1	-2270	-593
82	XTOUT	1954	-2178	27	Seg 5	886	2178	55	A2 I/O ports	-2270	-773
83	XTIN	2134	-2178	28	Seg 6	706	2178	56	A3 I/O ports	-2270	-953
1	V <sub>DD</sub>	2257	-1959	29	Seg 7	526	2178	57	A4 I/O ports	-2270	-1133
2	V <sub>SS</sub>	2257	-1779	30	Seg 8	346	2178	58	COM3/P3	-2270	-1602
3	CFIN/P1	2257	-1599	31	Seg 9	166	2178	59	COM4/P4	-2270	-1846
4	CFOUT/P2	2257	-1402	32	Seg 10	-14	2178				

Note: • The pin numbers are the QIP-80E mass-production package pin numbers.

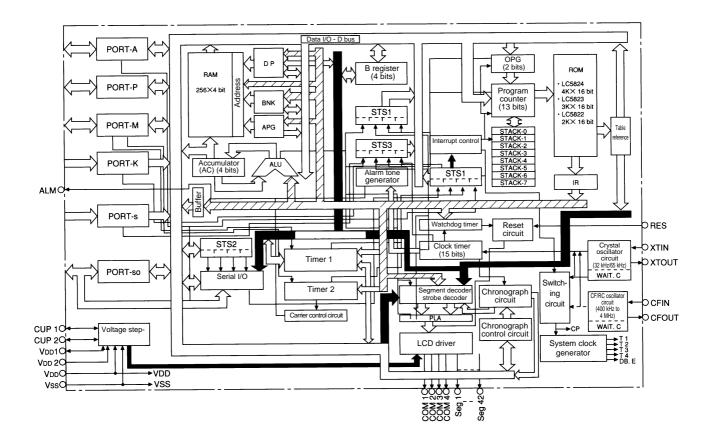
- The test pin (TST) must be connected to  $V_{\text{SS}}.$ 

• Pads number 42 and 43 in the chip version must be left open.

• Do not use solder dip techniques to mount the QIP-80E package version.

- In the chip version, the substrate must be either connected to  $V_{\mbox{SS}}$  or left open.

#### System Block Diagram



- RAM: Data memory
- ROM: Program memory
- DP: Data pointer register
- BNK: Bank register
- APG: RAM page flag
- AC: Accumulator
- ALU: Arithmetic and logic unit
- B: B register
- OPG: ROM page flag

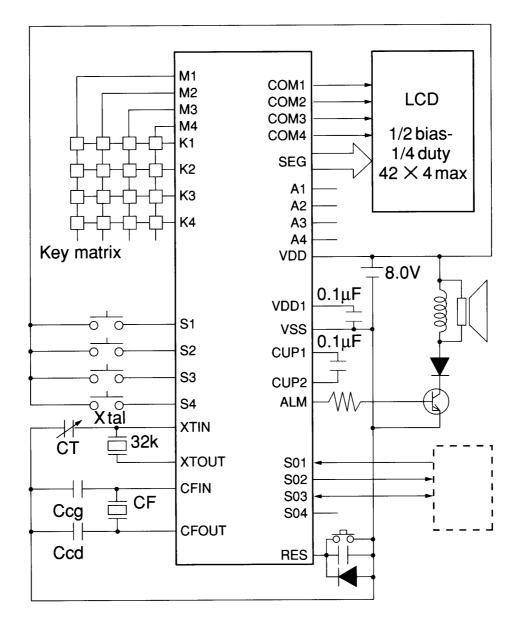
- PC: Program counter
- IR: Instruction register
- STS1: Status register 1
- STS2: Status register 2
- STS3: Status register 3
- STS4: Status register 4
- PLA: Programmed logic array used for segment data and strobe functions
- WAIT.C: Wait time counter

## **Pin Functions**

Pin No.	Pin	I/O	Function	Options	Status at reset
24 25	V <sub>DD</sub> V <sub>SS</sub>	-	Power supply		
25	VSS		LCD drive power supply		
30 29 28	V <sub>DD</sub> 1 V <sub>DD</sub> 2/BAK V <sub>DD</sub> 3		Power supply specifications         Ag         Li         EXTV           Pin blas         NON&/A6/2         1/3         NON&/A6/2         1/3         VID           VDD         O         O         O         O         O         O         O           VDD3         O         O         O         O         O         O         O           VDD3         O         O         O         O         O         O         O         O           VDD1         O	<ul> <li>Ag specifications</li> <li>Li specifications</li> <li>EXT-V specifications</li> </ul>	
42 43	CUP1 CUP2	_	Connections of the LCD power supply step-up (step-down) capacitors		
26 27	CFIN CFOUT	Input Output	System clock oscillator connections • Ceramic element connections (CF specifications) • RC component connections (RC specifications) *: This oscillator circuit is stopped when a STOP or SLOW instruction is executed.	<ul> <li>CF specifications</li> <li>RC specifications</li> <li>Unused</li> </ul>	
23 22	XTIN XTOUT	Input Output	Used for reference counting (clock specifications, LCD alternation frequency) and as the system clock. • 32-kHz crystal oscillator • 65-kHz crystal oscillator *: This oscillator circuit is stopped when a STOP instruction is executed.	<ul> <li>32-kHz specifications</li> <li>65-kHz specifications</li> <li>38-kHz specifications</li> <li>Unused</li> </ul>	
	хс	_	Used for the phase compensation capacitor connected between this pin and XTOUT and XTIN. This pin is only used in the chip product.		
67 68 69 70	S1 S2 S3 S4	Input	Input-only port • Input pins used to acquire input data to RAM • 1.95-ms and 7.8-ms chattering exclusion circuits included. • Pull-down resistors are built in. Note: the 1.95 ms and 7.8 ms values are for a ø0 of 32.768 kHz.	Presence or absence of low-level hold transistors	• Pull-down resistors enabled Note: After a reset is cleared, these pins go to the floating state.
71 72 73 74	K1 K2 K3 K4	Input	Input-only port Input pins used to acquire input data to RAM 1.95-ms and 7.8-ms chattering exclusion circuits included. Pull-down resistors are built in. Note: the 1.95 ms and 7.8 ms values are for a ø0 of 32.768 kHz.	Presence or absence of low-level hold transistors	• Pull-down resistors enabled Note: After a reset is cleared, these pins go to the floating state.
36 37 38 39	M1 M2 M3 M4	I/O	<ul> <li>I/O port</li> <li>Input pins used to acquire input data to RAM.</li> <li>Output pins used to output RAM data.</li> <li>M4 is also used as the TM1 external clock input in TM1 mode 3.</li> <li>M3 is also used for HEF8 halt mode clear control.</li> <li>*: The minimum period for clock signal inputs is twice the cycle time</li> <li>Pull-down resistors are built in.</li> </ul>	<ul> <li>Presence or absence of low-level hold transistors</li> <li>Output type: CMOS or p-channel</li> </ul>	<ul> <li>Pull-down resistors enabled</li> <li>Note: After a reset is cleared, these pins go to the floating state.</li> <li>Input mode</li> <li>The output latch data is set to 1.</li> </ul>
26 27 79 80	P1 P2 P3 P4	I/O	<ul> <li>I/O port</li> <li>Input pins used to acquire input data to RAM.</li> <li>Output pins used to output RAM data.</li> <li>Pull-down resistors are built in.</li> </ul>	The same as those for M1 to M4. However, only for valid ports.	The same as those for M1 to M4. However, only for valid ports.
76 77 78 79	A1 A2 A3 A4	I/O	<ul> <li>I/O port</li> <li>Input pins used to acquire input data to RAM.</li> <li>Output pins used to output RAM data.</li> <li>Pull-down resistors are built in.</li> <li>A1 is also used as the external interrupt request control input signal (INT).</li> </ul>	The same as those for M1 to M4.	The same as those for M1 to M4.

Pin No.	Pin	I/O		F	unction			Options	Status at reset
32 33 34 35	SO1 SO2 SO3 SO4	I/O	<ul> <li>I/O port</li> <li>Input pins used to acquire input data to RAM.</li> <li>Output pins used to output RAM data.</li> <li>Pull-down resistors are built in.</li> <li>SO1 to SO3 are also used as the serial interface pins.</li> <li>The serial interface function can be selected under program control.</li> <li>Pin functions:</li> <li>SO1: Serial input</li> <li>SO2: Serial output</li> <li>SO3: Serial clock</li> <li>The serial clock can be taken from either internal or external sources, and can be set up to detect either rising or falling edges under program control.</li> </ul>					Identical to M1 through M4	Identical to M1 through M4
31	ALM	Output	Output-only pin • A signal modula program contro		ø3, or ø4 c	can be outp	ut under		Low-level output
40	RES	Input	<ul> <li>The program co</li> <li>The reset input</li> <li>Either a pull-up</li> <li>Note: Application</li> </ul>	IC internal reset input • The program counter is set to point to location 00H. • The reset input level can be set to be either high or low. • Either a pull-up or a pull-down resistor is built in. Note: Applications must apply the reset signal level for at least 500 us to effect a reset.					or v
44 64 1 21	Seg 22 Seg 21 Seg 22 Seg 42	Output	LCD panel driv (1) Static (2) 1/2 bias 1/ (3) 1/2 bias 1/ (4) 1/2 bias 1/ (5) 1/3 bias 1/ (6) 1/3 bias 1/ One of items (1) General-purpos (1) CMOS outp (2) p-channel o (3) n-channel o One of items (1) The adoption o means that the LCD/general-pu Output latch co standby states	LCD panel drive outputs/general-purpose outputs  LCD panel drive				<ul> <li>Switching between LC drive output and general-purpose outp</li> <li>Switching between the LCD drive type option —Static</li> <li>—1/2 bias 1/2 duty</li> <li>—1/2 bias 1/3 duty</li> <li>—1/2 bias 1/4 duty</li> <li>—1/3 bias 1/4 duty</li> <li>—1/3 bias 1/4 duty</li> <li>General-purpose outp type switching</li> <li>—CMOS</li> <li>—p-channel open-dra</li> <li>—Standby mode output latch control</li> </ul>	<ul> <li>—All off</li> <li>* Determined by the master options</li> <li>• When used as general- purpose outputs:</li> <li>—High level</li> <li>—Low level</li> <li>* Determined by the master options</li> <li>Note: When a</li> <li>combination of LCD drive and general-purpose outputs is selected, these</li> <li>pins will be either:</li> <li>All lit/high-level output, or</li> </ul>
65 66 79 80	COM1 COM2 COM3 COM4	Output		lists which nat the lister ions when a Static O X X X X 32 Hz he "X" sym	pins are us d alternatio ø0 is 32.760 1/2 duty O X X X 32 Hz	ed in each n frequenci 8 kHz. 1/3 duty 0 0 0 X 42.7 Hz es that the c	1/4/duty	ıg	* In products with the CF specifications, the alternation frequency signal stops briefly.
41	TST	Input		<ul> <li>In the QIP-80 version, this pin must be connected to V<sub>SS</sub>.</li> <li>In the chip version, this pin must be left open or connected to</li> </ul>					
_	TEST TEST	_	Test pins. (These are not u	sed in the o	device user	interface.)			

Sample Application Circuit LCD : 1/2 bias — 1/4 duty



# **Oscillator Circuit Options**

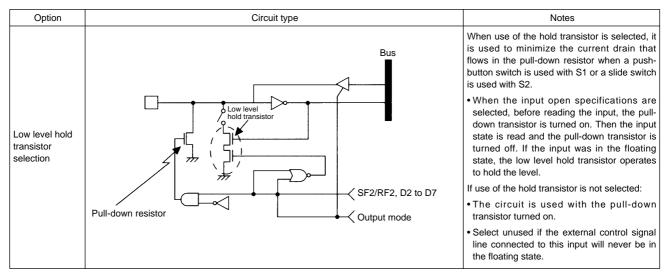
Option	Circuit type	Notes
RC & Xtal	CFIN CFIN S CFOUT T S CFOUT T S CFOUT T S CFOUT T T T T T T T T T T T T T	<ul> <li>The cycle time is 4 times the f1 period.</li> <li>The divider circuit outputs (ø1 through ø15) are used as the clock time base, the LCD drive waveform generation clock, and for S/K port chattering prevention.</li> <li>OSC1 is stopped by the execution of a SLOW instruction.</li> </ul>
CF & Xtal • 400 kHz (CF) • 4 MHz (CF)	CFIN CFIN CFI T1 CFU T1 T2 T3 T3 T4 T4 T4 T4 T4 T4 T4 T4 T4 T4 T4 T4 T4	<ul> <li>The cycle time is 4 times n times the f1 period. (n:1)</li> <li>The divider circuit outputs (ø1 through ø15) are used as the clock time base, the LCD drive waveform generation clock, and for S/K port chattering prevention.</li> <li>OSC1 is stopped by the execution of a SLOW instruction.</li> </ul>
RC	VSS TI VSS TI VS	<ul> <li>The cycle time is 4 times the f1 period.</li> <li>The divider circuit outputs (ø1 through ø15) are used as the clock time base, the LCD drive waveform generation clock, and for S/K port chattering prevention.</li> </ul>

Option	Circuit type	Notes
CF • 400 kHz • 4 MHz	CFIN 50 CFIN 50 0 1/n 1/n T2 T3 T4 HALT VSS	<ul> <li>The cycle time is 4 times n times the f1 period. (n:1)</li> <li>The divider circuit outputs (ø1 through ø15) are used as the clock time base, the LCD drive frequency generation clock, and for S/K port chattering prevention.</li> </ul>
Xtal • 32 kHz • 55 kHz	CFIN CFOUT CFOUT CFOUT CFOUT CFOUT STOP UIL T2 T3 T4 HALT HALT UIL UIL T2 T3 T4 HALT	<ul> <li>The cycle time is 4 times the f2 period.</li> <li>The divider circuit outputs (ø1 through ø15) are used as the clock time base, the LCD drive waveform generation clock, and for S/K port chattering prevention.</li> <li>Note that the CFIN and CFOUT pins are switched over to function as the P1 and P2 pins.</li> </ul>

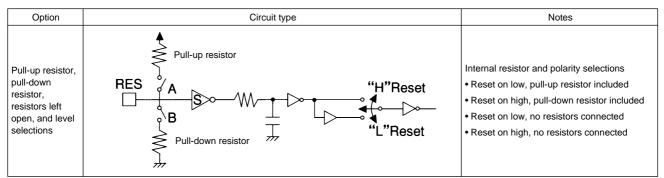
## **Crystal Oscillator Circuit Options**

Option	Circuit type	Notes
Used at 32 kHz	$\begin{array}{c} & & \\ & & \\ & & \\ & \\ & \\ & \\ & \\ & \\ $	The resistor RD is built into the IC when this circuit is used at 32 kHz.
Used at 38 kHz Used at 65 kHz	Cg XTIN Cg Rf Cd XTOUT Vss	<ul> <li>The cycle time is 4 times n times the f1 period. (n:2)</li> <li>The divider circuit outputs (ø1 through ø15) are used as the clock time base, the LCD drive frequency generation clock, and for S/K port chattering prevention.</li> <li>OSC1 is stopped by the execution of a SLOW instruction.</li> </ul>

#### **Input Port Options**



#### **RES** Pin



#### **Mask Option List**

Voltage specifications

- Ag specifications
- Li specifications
- EXT-V specifications

#### LCD driver

- Static
- 1/2 bias 1/2 duty
  - 1/2 bias 1/3 duty
  - 1/2 bias 1/4 duty
  - 1/3 bias 1/3 duty
  - 1/3 bias 1/4 duty
  - Unused

Segment port states during a reset

- LCD driver pins
- All lit
- All off
- CMOS p/n-channel pins
- High level
- Low level

#### Oscillator specifications

- CF only (ceramic oscillator element)
- RC only (using a resistor and a capacitor)
- Crystal only
- CF + crystal
- RC + crystal

#### CF

- 400 kHz
- 800 kHz
- 1 MHz
- 2 MHz
- 4 MHz

#### RC

- 400 kHz
- 800 kHz
- 1 MHz

#### Crystal

- 32 kHz
- 65 kHz
- 38 kHz

#### LCD alternation frequency

- SLOW
- TYP
- FAST

#### External reset circuit

- RES pin
- RES pin + S1 to S4 pressed at the same time

Internal reset circuit (power on reset)

- Selected
- Disabled

#### RES pin

- Reset on low, pull-up resistor included
- Reset on high, pull-down resistor included
- Reset on low, no resistors connected
- · Reset on high, no resistors connected
- Alarm output initial level
- Low level
- High level

#### Chronometer and strobe selection

- 00H
- 10H
- 00H & 10H
- Unused

Port S low level hold transistors

- Low level hold transistors present
- Low level hold transistors disabled

#### Port K low level hold transistors

- · Low level hold transistors present
- Low level hold transistors disabled

#### Port M low level hold transistors

- Low level hold transistors present
- Low level hold transistors disabled

#### Port P low level hold transistors

- · Low level hold transistors present
- Low level hold transistors disabled

#### Port SO low level hold transistors

- Low level hold transistors present
- Low level hold transistors disabled

#### Port A low level hold transistors

- Low level hold transistors present
- Low level hold transistors disabled

#### M1 to M4 outputs

- CMOS
- p-channel
- n-channel

#### P1 to P4 outputs

- CMOS
- p-channel
- n-channel

## A1 to A4 outputs

- CMOS
- p-channel n-channel

These electrical characteristics are provisional and the values are subject to change.

## Ag Specifications

# Absolute Maximum Ratings at Ta = 25 $^{\circ}C$ $\pm 2^{\circ}C,$ $V_{SS}$ = 0 V

Parameter	Symbol	Conditions and applicable pins		Unit		
Parameter	Symbol	Conditions and applicable pins	min	typ	max	Unit
	V <sub>DD</sub>		-0.3		+4.0	V
	V <sub>DD</sub> 1		-0.3		+4.0	V
Maximum supply voltage	V <sub>DD</sub> 2		-0.3		+5.5	V
	V <sub>DD</sub> 3	For 1/3-bias LCD drive techniques	-0.3		+4.0	V
	V <sub>DD</sub> 3	For LCD drive techniques other than 1/3 bias	-0.3		+4.0	V
Maximum input voltage	V <sub>IN</sub> 1	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, RES,TST	-0.3		V <sub>DD</sub> + 0.3	V
Maximum output voltage	V <sub>OUT</sub> 1	M1 to M4, A1 to A4, SO1 to SO4, ALM, CUP2 (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode)	-0.3		+0.3	v
	V <sub>OUT</sub> 2	SEGOUT, COM1 to COM4, CUP1	-0.3		V <sub>DD</sub> 3 + 0.3	V
Operating temperature	Topg		-20		+65	°C
Storage temperature	Tstg		-30		+125	°C

## Allowable Operating Ranges at $Ta=25^\circ C \pm 2^\circ C, \, V_{SS}=0 \; V$

Parameter	Symbol Conditions and applicable pins			Unit		
Falanielei	Symbol		min	typ	max	Unit
	V <sub>DD</sub> V <sub>DD</sub> 1	VBAK = V <sub>DD</sub> 1	1.3		1.65	V
Supply voltage	V <sub>DD</sub> 2		2.4		3.3	V
	V <sub>DD</sub> 3	For 1/3-bias LCD drive techniques	3.7		4.95	V
	V <sub>DD</sub> 3	For LCD drive techniques other than 1/3 bias	2.4		3.3	
High-level input voltage	VIH	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES	V <sub>DD</sub> – 0.2		V <sub>DD</sub>	V
Low-level input voltage	VIL	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES	0		0.2	V
Operating frequency	fopg	Ta = −20 to +65°C	32		33	kHz

# Electrical Characteristics at Ta = 25°C $\pm$ 2°C, V<sub>SS</sub> = 0 V, V<sub>DD</sub> = V<sub>DD</sub>1

Parameter	Cumhal	Conditions and applicable size		Unit		
Parameter	Symbol	Conditions and applicable pins	min	typ	max	Unit
	R <sub>IN</sub> 1A	$V_{DD}$ = 1.5 V, Low level hold transistor V <sub>IN</sub> = 0.35 V <sub>DD</sub> *1 Figure 1	50		500	kΩ
	R <sub>IN</sub> 1B	$V_{DD}$ = 1.5 V, Programmable pull-down resistor $V_{IN}$ = 0.7 $V_{DD}$ *1 Figure 1	50		1000	kΩ
Input resistance	R <sub>IN</sub> 2A	$V_{DD}$ = 1.5 V, Low level hold transistor V <sub>IN</sub> = 0.35 V <sub>DD</sub> , Input mode *2, Figure 1	50		500	kΩ
	R <sub>IN</sub> 2B	$V_{DD}$ = 1.5 V, Programmable pull-down resistor V <sub>IN</sub> = 0.7 V <sub>DD</sub> , Input mode *2, Figure 1	50		1000	kΩ
	R <sub>IN</sub> 3	$V_{DD}$ = 1.5 V, The RES pin pull-up/pull-down resistor $V_{IN}$ = 0.7 $V_{DD}/0.3 V_{DD}$	10		300	kΩ
High-level output voltage	V <sub>OH</sub> 1	$V_{DD}$ = 1.3 V, I <sub>OH</sub> = -250 µA, ALM	V <sub>DD</sub> – 0.65			V
Low-level output voltage	V <sub>OL</sub> 1	V <sub>DD</sub> = 1.3 V, I <sub>OL</sub> = 250 μA, ALM			0.65	V
High-level output voltage	V <sub>OH</sub> 2	$\label{eq:VDD} \begin{array}{l} V_{DD}$ = 1.5 V, M1 to 4, A1 to 4, SO1 to 4 I_{OH} = -20 $\mu$ A, (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode)	V <sub>DD</sub> – 0.2			V
Low-level output voltage	V <sub>OL</sub> 2	$\label{eq:VDD} \begin{array}{l} V_{DD} = 1.5 \ V, \ M1 \ to \ 4, \ A1 \ to \ 4, \ SO1 \ to \ 4 \\ I_{OL} = 20 \ \mu A, \\ (With \ M1 \ to \ M4, \ A1 \ to \ A4, \ and \ SO1 \ to \ SO4 \ in \ output \ mode) \end{array}$			0.2	V

Parameter	Symbol	Conditions and applicable pins		Ratings		Unit
Farameter	Symbol		min	typ	max	Unit
Segment driver output impedance						
[When Set Up as CMOS Output Po	rts]					
High-level output voltage	V <sub>OH</sub> 3	$V_{DD}$ = 1.5 V, $I_{OH}$ = -3 µA, Segment 1 to 42	V <sub>DD</sub> – 1.0			V
Low-level output voltage	V <sub>OL</sub> 3	$V_{DD}$ = 1.5 V, $I_{OL}$ = 3 µA, Segment 1 to 42			1.0	V
[When Set Up as P-Channel Open-	Drain Output	Ports]				
High-level output voltage	V <sub>OH</sub> 3	$V_{DD}$ = 1.5 V, $I_{OH}$ = -3 µA, Segment 1 to 42		0.3	1.0	V
Output off leakage current	I <sub>OFF</sub>	$V_{DD}$ = 1.5 V, $V_{OL}$ = $V_{SS}$ , Segment 1 to 42			1.0	μA
[Static Drive]						
High-level output voltage	V <sub>OH</sub> 3	V <sub>DD</sub> = 1.5 V, I <sub>OH</sub> = -0.4 μA, SEGOUT	V <sub>DD</sub> 2-0.2			V
Low-level output voltage	V <sub>OL</sub> 3	V <sub>DD</sub> = 1.5 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 4	V <sub>DD</sub> = 1.5 V, I <sub>OH</sub> = -4 μA, COM1	V <sub>DD</sub> 2-0.2			V
Low-level output voltage	V <sub>OL</sub> 4	V <sub>DD</sub> = 1.5 V, I <sub>OL</sub> = 4 μA, COM1			0.2	V
[Duplex Drive (1/2 bias - 1/2 duty)]			· ·			
High-level output voltage	V <sub>OH</sub> 3	V <sub>DD</sub> = 1.5 V, I <sub>OH</sub> = -0.4 μA, SEGOUT	V <sub>DD</sub> 2-0.2			V
Low-level output voltage	V <sub>OL</sub> 3	V <sub>DD</sub> = 1.5 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 4	$V_{DD}$ = 1.5 V, $I_{OH}$ = -4 $\mu$ A, COM1 to COM2	V <sub>DD</sub> 2-0.2			V
Middle-level output voltage	V <sub>OM</sub>	$V_{DD}$ = 1.5 V, $I_{OH}$ = -4 $\mu$ A, $I_{OL}$ = 4 $\mu$ A, COM1 to COM2	V <sub>DD</sub> 1 - 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 4	$V_{DD}$ = 1.5 V, $I_{OL}$ = 4 $\mu$ A, COM1 to COM2			0.2	V
[1/2 Bias - 1/3 Duty and 1/2 Bias - 2	/4 Duty Drive	) 2]	- I I		1	
High-level output voltage	V <sub>OH</sub> 3	V <sub>DD</sub> = 1.5 V, I <sub>OH</sub> = -0.4 μA, SEGOUT	V <sub>DD</sub> 2-0.2			V
Low-level output voltage	V <sub>OL</sub> 3	V <sub>DD</sub> = 1.5 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 4	$V_{DD}$ = 1.5 V, $I_{OH}$ = -4 µA, COM1 to COM3 (1/3 duty) COM1 to COM4 (1/4 duty)	V <sub>DD</sub> 2 – 0.2			V
Middle-level output voltage	V <sub>OM</sub>	$V_{DD}$ = 1.5 V, $I_{OH}$ = -4 µA, $I_{OL}$ = 4 µA, COM1 to COM3 (1/3 duty), COM1 to COM4 (1/4 duty)	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 4	$V_{DD}$ = 1.5 V, $I_{OL}$ = 4 µA, COM1 to 2 COM1 to COM3 (1/3 duty), COM1 to COM4 (1/4 duty)			0.2	V
[1/3 Bias - 1/3 Duty and 1/3 Bias - 2	1/4 Duty Drive	) )	· · ·			
High-level output voltage	V <sub>OH</sub> 3	$V_{DD}$ = 1.5 V, $I_{OH}$ = -0.4 µA, SEGOUT	V <sub>DD</sub> 3-0.2			V
M1-level output voltage	V <sub>OM</sub> 1–3	$V_{DD}$ = 1.5 V, $I_{OH}$ = -0.4 $\mu$ A, $I_{OL}$ = 0.4 $\mu$ A, SEGOUT	V <sub>DD</sub> 2-0.2		V <sub>DD</sub> 2 + 0.2	V
M2-level output voltage	V <sub>OM</sub> 2–3	$V_{DD}$ = 1.5 V, $I_{OH}$ = -0.4 $\mu$ A, $I_{OL}$ = 0.4 $\mu$ A, SEGOUT	V <sub>DD</sub> 1 - 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 3	V <sub>DD</sub> = 1.5 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 4	$V_{DD}$ = 1.5 V, $I_{OH}$ = -4 µA, COM1 to COM3 (1/3 duty) COM1 to COM4 (1/4 duty)	V <sub>DD</sub> 3 - 0.2			V
M1-level output voltage	V <sub>OM</sub> 1–4	$\label{eq:VDD} \begin{array}{l} V_{DD} = 1.5 \ V, \ I_{OH} = -4 \ \muA, \ I_{OL} = 4 \ \muA, \\ \ COM1 \ to \ COM3 \ (1/3 \ duty), \ COM1 \ to \ COM4 \ (1/4 \ duty) \end{array}$	V <sub>DD</sub> 2 – 0.2		V <sub>DD</sub> 2 + 0.2	V
M2-level output voltage	V <sub>OM</sub> 2–4	$      V_{DD} = 1.5 \text{ V}, \text{ I}_{OH} = -4  \mu\text{A}, \text{ I}_{OL} = 4  \mu\text{A}, \\ \text{COM1 to COM3 (1/3 duty), COM1 to COM4 (1/4 duty) } $	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 4	$V_{DD}$ = 1.5 V, $I_{OL}$ = 4 µA, COM1 to COM3 (1/3 duty), COM1 to COM4 (1/4 duty)			0.2	V

Deservation	O week at			Ratings		- Unit
Parameter	Symbol	Conditions and applicable pins	min	typ	max	
[Output Voltage]						
LCD drive method: 1/3 bias						
(doubler)	V <sub>DD</sub> 2	$V_{DD}$ = 1.35 V, fopg = 32.768 kHz, C1 to C3 = 0.1 $\mu F$ Figure 2	2.5			V
(tripler)	V <sub>DD</sub> 3	$V_{DD}$ = 1.35 V, fopg = 32.768 kHz, C1 to C3 = 0.1 $\mu F$ Figure 2	3.75			V
LCD drive method: 1/2 bias		· · · · ·				
(doubler)	V <sub>DD</sub> 2	$V_{DD}$ = 1.35 V, fopg = 32.768 kHz, C1 to C2 = 0.1 $\mu F$ Figure 3	2.5			V
[Current Drain (with the backup flag	cleared)]	· · · · ·				
LCD drive method: 1/3 bias	I <sub>DD</sub>	$\label{eq:VDD} \begin{array}{l} V_{DD} = 1.5 \mbox{ V, In halt mode, C1 to C3} = 0.1  \mu\mbox{F, CI} = 25  k\Omega, \\ Figure 2, \mbox{ Co} = Cg = 20  p\mbox{F, 32.768 kHz Xtal} \end{array}$		3.5		μA
LCD drive methods other than 1/3 bias	I <sub>DD</sub>	$\label{eq:VDD} \begin{array}{l} V_{DD} = 1.5 \mbox{ V, In halt mode, C1} = C2 = 0.1  \mu \mbox{F, CI} = 25  k\Omega, \\ \mbox{Figure 3, Co} = Cg = 20  p \mbox{F, 32.768  Hz  Xtal \end{array}$		2.0		μA
Oscillator start voltage	Vstt	Co = Cg = 20 pF, Cl = 25 kΩ, Figure 3, 32.768 kHz Xtal			1.35	V
Oscillator hold voltage	V <sub>hold</sub>	$V_{BAK} = V_{DD}$ 1, Cl = 25 k $\Omega$ , Figures 2 and 3 Co = Cg = 20 pF, 32.768 kHz Xtal	1.3		1.65	V
Oscillator start time	Tstt	$V_{DD}$ = 1.35 V, Cl = 25 k $\Omega$ , Figure 4, Co = Cg = 20 pF, 32.768 kHz Xtal			10	sec
	10P	XC	8	10	12	pF
Oscillator correction capacitance	20P	XTOUT	16	20	24	pF

# Li Specifications Absolute Maximum Ratings at $Ta=25^{\circ}C$ $\pm2^{\circ}C,$ $V_{SS}=0$ V

Parameter	Symbol	Conditions and applicable pipe		Ratings		Unit
Parameter	Symbol	Conditions and applicable pins	min	typ	max	
	V <sub>DD</sub>		-0.3		+4.0	V
	V <sub>DD</sub> 1	$V_{BAK} = V_{DD}1 \text{ or } V_{DD}2$	-0.3		+4.0	V
Maximum supply voltage	V <sub>DD</sub> 2		-0.3		+4.0	V
	V <sub>DD</sub> 3	(LCD drive method: 1/3 bias)	-0.3		+5.5	V
	V <sub>DD</sub> 3	(LCD drive methods other than 1/3 bias)	-0.3		+4.0	V
Maximum input voltage	V <sub>IN</sub> 1	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES, TST	-0.3		V <sub>DD</sub> + 0.3	V
Maximum output voltage (LCD drive method: 1/3 b <sup>ias)</sup>	V <sub>OUT</sub> 1	M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode) ALM, CUP2	-0.3		V <sub>DD</sub> + 0.3	V
(	V <sub>OUT</sub> 2	SEGOUT, COM1 to COM4, CUP1	-0.3		V <sub>DD</sub> 3 + 0.3	V
(LCD drive methods other than 1/3 bias)	V <sub>OUT</sub> 2	M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode) ALM, SEGOUT, COM1 to COM4, CUP1, CUP2	-0.3		V <sub>DD</sub> + 0.3	V
Operating temperature	Topg		-20		+65	°C
Storage temperature	Tstg		-30		+125	°C

# Allowable Operating Ranges at Ta = $25^{\circ}C \pm 2^{\circ}C$ , $V_{SS} = 0 V$

Parameter	Symbol	Conditions and applicable pine	Ratings			Unit
Parameter	Symbol	Conditions and applicable pins	min	typ	max	
	$\begin{pmatrix} V_{DD} \\ V_{DD}^2 \end{pmatrix}$	$V_{BAK} = V_{DD} /2$ (With the backup flag cleared)	2.0		3.6	V
Supply voltage	$\begin{pmatrix} V_{DD} \\ V_{DD}^2 \end{pmatrix}$	$V_{BAK} = V_{DD}$ (With the backup flag uncleared)	1.3		3.6	V
	V <sub>DD</sub> 3	(LCD drive method: 1/3-bias)	3.9		5.0	V
	V <sub>DD</sub> 3	(LCD drive methods other than 1/3 bias)		$V_{DD}3 = V_{DD}2$		V
High-level input voltage	V <sub>IH</sub>	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES	V <sub>DD</sub> – 0.4		V <sub>DD</sub>	v
Low-level input voltage	VIL	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES	0		0.4	v
Operating frequency	fopg	Ta = −20 to +65°C	32		33	kHz

# Electrical Characteristics at Ta = 25°C $\pm 2^{\circ}C,$ $V_{SS}$ = 0 V, $V_{DD}$ = $V_{DD}2$

Parameter	Symbol	Conditions and applicable pins	Ratings			Unit
Falameter			min	typ	max	Unit
	R <sub>IN</sub> 1A	$V_{DD}$ = 3.0 V, $V_{IN}$ = 0.35 $V_{DD}$ Low level hold transistor *1, Figure 5	50		500	kΩ
	R <sub>IN</sub> 1B	V <sub>DD</sub> = 3.0 V, V <sub>IN</sub> = 0.7V <sub>DD</sub> Programmable pull-down resistor *1, Figure 5	50		1000	kΩ
Input resistance	R <sub>IN</sub> 2A	$V_{DD}$ = 3.0 V, input mode, Low level hold transistor *1, $V_{IN}$ = 0.35 $V_{DD},$ Figure 5	50		500	kΩ
R <sub>IN</sub> 2B	$V_{DD}$ = 3.0 V, Programmable pull-down resistor, *2, V <sub>IN</sub> = 0.7 V <sub>DD</sub> , input mode, Figure 5	50		1000	kΩ	
	R <sub>IN</sub> 3	$V_{DD}$ = 3.0 V, RES pin pull-up/pull-down resistor $V_{IN}$ = 0.7 $V_{DD}/0.3 V_{DD}$	10		300	kΩ

# Electrical Characteristics at Ta = 25°C $\pm 2^{\circ}C,$ $V_{SS}$ = 0 V, $V_{DD}$ = $V_{DD}2$

Parameter	Sumbol	Conditions and applicable pins		Ratings		Unit
Parameter	Symbol	Conditions and applicable pins	min	typ	max	Unit
High-level output voltage	V <sub>OH</sub> 1	V <sub>DD</sub> = 2.5 V, I <sub>OH</sub> = -250 μA, ALM	V <sub>DD</sub> – 0.65			V
Low-level output voltage	V <sub>OL</sub> 1	V <sub>DD</sub> = 2.5 V, I <sub>OL</sub> = 250 μA, ALM			0.65	V
High-level output voltage	V <sub>OH</sub> 2	$V_{DD}$ = 3.0 V, $I_{OH}$ = -40 µA, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode)	V <sub>DD</sub> – 0.4			V
Low-level output voltage	V <sub>OL</sub> 2	$V_{DD}$ = 3.0 V, $I_{OL}$ = 40 µA, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode)			0.4	V
Segment driver output impedance						
[When Set Up as CMOS Output P	orts]					
High-level output voltage	V <sub>OH</sub> 3	$V_{DD}$ = 3.0 V, $I_{OH}$ = -5 µA, Segment 1 to 42	V <sub>DD</sub> – 1			V
Low-level output voltage	V <sub>OL</sub> 3	$V_{DD}$ = 3.0 V, I <sub>OL</sub> = 5 µA, Segment 1 to 42			1	V
[When Set Up as P-Channel Oper	-Drain Output	Ports]				
High-level output voltage	V <sub>OH</sub> 3	$V_{DD}$ = 2.5 V, $I_{OH}$ = -10 µA, Segment 1 to 42		0.3	1	V
Output off leakage current	I <sub>OFF</sub>	$V_{DD} = 3.0 \text{ V}, \text{ V}_{OL} = \text{V}_{SS}$			1	μA
[Static Drive]		-				
High-level output voltage	V <sub>OH</sub> 3	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 μA, SEGOUT	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 3	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 4	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -4 µA, COM1	V <sub>DD</sub> – 0.2			V
Low-level output voltage	V <sub>OL</sub> 4	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 4 μA, COM1			0.2	V
[Duplex Drive (1/2 bias - 1/2 duty)]						
High-level output voltage	V <sub>OH</sub> 3	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 μA, SEGOUT	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 3	$V_{DD} = 3.0 \text{ V}, \text{ I}_{OL} = 0.4 \mu\text{A}, \text{ SEGOUT}$			0.2	V
High-level output voltage	V <sub>OH</sub> 4	$V_{DD} = 3.0 \text{ V}, I_{OH} = -4 \mu \text{A}, \text{COM1 to COM2}$	V <sub>DD</sub> – 0.2			V
Middle-level output voltage	V <sub>OM</sub>	$V_{DD}$ = 3.0 V, $I_{OH}$ = -4 $\mu$ A, $I_{OL}$ = 4 $\mu$ A, COM1 to COM2	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 4	$V_{DD} = 3.0 \text{ V}, I_{OL} = 4 \mu \text{A}, \text{COM1 to COM2}$			0.2	V
[1/2 Bias - 1/3 Duty and 1/2 Bias -	1/4 Duty Drive	) )				
High-level output voltage	V <sub>OH</sub> 3	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 μA, SEGOUT	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 3	$V_{DD} = 3.0 \text{ V}, \text{ I}_{OL} = 0.4 \mu\text{A}, \text{ SEGOUT}$			0.2	V
High-level output voltage	V <sub>OH</sub> 4	$V_{DD}$ = 3.0 V, $I_{OH}$ = -4 µA, COM1 to COM3 (1/3 duty) COM1 to COM4 (1/4 duty)	V <sub>DD</sub> – 0.2			V
Middle-level output voltage	V <sub>OM</sub>	$V_{DD} = 3.0 \text{ V}, I_{OH} = -4 \ \mu\text{A}, I_{OL} = 4 \ \mu\text{A},$ COM1 to COM3 (1/3 duty) COM1 to COM4 (1/4 duty)	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 4	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 4 μA, COM1 to COM3 (1/3 duty) COM1 to COM4 (1/4 duty)			0.2	V

Parameter	Symbol	Conditions and applicable pins		Ratings		
i arameter	Gymbol		min	typ	max	Unit
[1/3 Bias - 1/3 Duty and 1/3 Bias - 1	/4 Duty Drive	e]				
High-level output voltage	V <sub>OH</sub> 3	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 µA, SEGOUT	V <sub>DD</sub> 3-0.2			V
M1-level output voltage	V <sub>OM</sub> 1-3	$V_{DD}$ = 3.0 V, $I_{OH}$ = -0.4 $\mu$ A, $I_{OL}$ = 0.4 $\mu$ A, SEGOUT	V <sub>DD</sub> 2-0.2		V <sub>DD</sub> 2 + 0.2	V
M2-level output voltage	V <sub>OM</sub> 2-3	$V_{DD}$ = 3.0 V, $I_{OH}$ = -0.4 $\mu$ A, $I_{OL}$ = 0.4 $\mu$ A, SEGOUT	V <sub>DD</sub> 1 - 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 3	$V_{DD} = 3.0 \text{ V}, \text{ I}_{OL} = 0.4 \mu\text{A}, \text{ SEGOUT}$			0.2	V
High-level output voltage	V <sub>OH</sub> 4	$\label{eq:VDD} \begin{array}{l} V_{DD}=3.0 \text{ V}, \text{ I}_{OH}=-4 \ \mu\text{A},\\ \text{COM1 to COM3 (in 1/3 duty mode)}\\ \text{COM1 to COM4 (in 1/4 duty mode)} \end{array}$	V <sub>DD</sub> 3 – 0.2			V
M1-level output voltage	V <sub>OH</sub> 1–4		V <sub>DD</sub> 2 - 0.2		V <sub>DD</sub> 2 + 0.2	V
M2-level output voltage	V <sub>OM</sub> 2–4	$ \begin{array}{l} V_{DD}=3.0 \text{ V}, \text{ I}_{OH}=-4 \ \mu\text{A}, \text{ I}_{OL}=4 \ \mu\text{A}, \\ \text{COM1 to COM3 (in 1/3 duty mode)} \\ \text{COM1 to COM4 (in 1/4 duty mode)} \end{array} $	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 4	$V_{DD}$ = 3.0 V, $I_{OL}$ = 4 µA, COM1 to COM3 (in 1/3 duty mode) COM1 to COM4 (in 1/4 duty mode)			0.2	V
[Output Voltage]						
LCD drive method: 1/3 bias						
(halver)	V <sub>DD</sub> 1	$V_{DD}$ = 3.0 V, fopg = 32.768 kHz, C1 to C4 = 0.1 µF, Figure 6	1.35			V
(tripler)	V <sub>DD</sub> 3	$V_{DD}$ = 3.0 V, fopg = 32.768 kHz, C1 to C4 = 0.1 µF, Figure 6	4.1			V
LCD drive method: 1/2 bias			· · ·			
(halver)	V <sub>DD</sub> 1	$V_{DD} = 3.0 \text{ V}$ , fopg = 32.768 kHz, C1 = C2 = 0.1 µF, Figure 7	1.35			V
[Current Drain (With the backup flag	cleared)]					
LCD drive method: 1/3 bias	I <sub>DD</sub>	$V_{DD}$ = 3.0 V, Halt mode C1 to C4 = 0.1 µF, C1 = 25 kΩ, Figure 6 Co = Cg = 20 pF, 32.768 kHz Xtal		2.0		μA
LCD drive methods other than 1/3 bias	I <sub>DD</sub>	$V_{DD}$ = 3.0 V, Halt mode C1 = C2 = 0.1 µF, CI = 25 kΩ, Figure 7 Co = Cg = 20 pF, 32.768 kHz Xtal		1.0		μA
Oscillator start capacitor	Vstt	$V_{DD}$ 1 = $V_{DD}$ , CI = 25 k $\Omega$ , Figure 4 Co = Cg = 20 pF, 32.768 kHz Xtal			1.35	V
Oscillator hold voltage (with the backup flag cleared)	V <sub>HOLD</sub>	$V_{BAK}$ = $V_{DD}$ 1 = $V_{DD}/2,$ CI = 25 kΩ, Figures 6 and 7 Co = Cg = 20 pF, 32.768 kHz Xtal	2.6			V
Oscillator start time	Tstt	$V_{DD}$ 1 = $V_{DD}$ = 1.35 V, Cl = 25 k $\Omega$ , Figure 4 Co = Cg = 20 pF, 32.768 kHz Xtal			10	sec
Oscillator correction capacitance	10P	XC	8	10	12	pF
Oscillator correction capacitance	20P	XTOUT	16	20	24	pF

# EXT-V Specifications Absolute Maximum Ratings at Ta = 25°C $\pm 2^{\circ}C,$ $V_{SS}$ = 0 V

Parameter	Symbol	Conditions and applicable pipe		Ratings		Unit
Falameter	Symbol	Conditions and applicable pins	min	typ	max	Unit
	V <sub>DD</sub>		-0.3		+4.0	V
	V <sub>DD</sub> 1		-0.3		+4.0	V
Maximum supply voltage	V <sub>DD</sub> 2		-0.3		+4.0	V
	V <sub>DD</sub> 3	(LCD drive method: 1/3 bias)	-0.3		+5.5	V
	V <sub>DD</sub> 3	(LCD drive methods other than 1/3 bias)	-0.3		+4.0	V
Maximum input voltage	V <sub>IN</sub> 2	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES, TST	-0.3		V <sub>DD</sub> + 0.3	V
Maximum output voltage (LCD drive method: 1/3 bias)	V <sub>OUT</sub> 2	M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode) ALM, CUP2	-0.3		V <sub>DD</sub> + 0.3	V
(,	V <sub>OUT</sub> 3	SEGOUT, COM1 to COM4, CUP1	-0.3		V <sub>DD</sub> 3 + 0.3	V
(LCD drive methods other than 1/3 bias)	V <sub>OUT</sub> 2	M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode) ALM, SEGOUT, COM1 to COM4, CUP1	-0.3		V <sub>DD</sub> + 0.3	V
Operating temperature	Topg		-20		+65	°C
Storage temperature	Tstg		-30		+125	°C

# Allowable Operating Ranges at Ta = $25^{\circ}C \pm 2^{\circ}C$ , $V_{SS} = 0 V$

Parameter	Sumbol	Conditions and applicable nine	Ratings			Unit
Parameter	Symbol	Conditions and applicable pins	min	typ	max	
Supply voltage	V <sub>DD</sub> 1		1.3		3.6	V
	V <sub>DD</sub> V <sub>DD</sub> 2		2.0		3.6	v
	V <sub>DD</sub> 3	(LCD drive method: 1/3-bias)	3.9		5.0	V
	V <sub>DD</sub> 3	(LCD drive methods other than 1/3 bias)	$V_{DD}3 = V_{DD}2$			V
High-level input voltage	V <sub>IH</sub>	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES	V <sub>DD</sub> – 0.4		V <sub>DD</sub>	V
Low-level input voltage	V <sub>IL</sub>	S1 to S4, K1 to K4, M1 to M4, A1 to A4, SO1 to SO4, (With M1 to M4, A1 to A4, and SO1 to SO4 in input mode) RES	0		0.4	v
Operating frequency	fopg	Ta = -20 + 65°C	32		33	kHz

# Electrical Characteristics at Ta = 25°C $\pm 2^{\circ}C,$ $V_{SS}$ = 0 V, $V_{DD}$ = $V_{DD}2$

Parameter	Symbol	Symbol Conditions and applicable pins		Ratings		
Falameter			min	typ	max	Unit
	R <sub>IN</sub> 1A	$V_{DD}$ = 3.0 V, $V_{IN}$ = 0.35 $V_{DD},$ Low level hold transistor *1, Figure 5	50		500	kΩ
	R <sub>IN</sub> 1B	$V_{DD}$ = 3.0 V, $V_{IN}$ = 0.7 $V_{DD},$ Programmable pull-down resistor *1, Figure 5	50		1000	kΩ
Input resistance	R <sub>IN</sub> 2A	$V_{DD}$ = 3.0 V, $V_{IN}$ = 0.35 $V_{DD},$ Input mode, Low level hold transistor *1, Figure 5	50		500	kΩ
	R <sub>IN</sub> 2B	$V_{DD}$ = 3.0 V, $V_{IN}$ = 0.7 $V_{DD}$ , input mode, Programmable pull-down resistor *2, Figure 5	50		1000	kΩ
	R <sub>IN</sub> 3	$V_{DD}$ = 3.0 V, $V_{IN}$ = 0.7 $V_{DD}/0.3 V_{DD}$ RES pin pull-up/pull-down resistor	10		300	kΩ

Parameter	Symbol	Conditions and applicable pins		Ratings		Unit
raidilleter	Symbol		min	typ	max	Offic
High-level output voltage	V <sub>OH</sub> 1	$V_{DD} = 2.5 \text{ V}, \text{ I}_{OH} = -250 \mu\text{A}, \text{ ALM}$	V <sub>DD</sub> – 0.65			V
Low-level output voltage	V <sub>OL</sub> 1	V <sub>DD</sub> = 2.5 V, I <sub>OL</sub> = 250 μA, ALM			0.65	V
High-level output voltage	V <sub>OH</sub> 2	$V_{DD}$ = 3.0 V, $I_{OH}$ = -40 µA, M1 to M4, A1 to A4, SO1 to SO4 (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode)	V <sub>DD</sub> - 0.4			V
Low-level output voltage	V <sub>OL</sub> 2	$V_{DD}$ = 3.0 V, $I_{OL}$ = 40 µA, M1 to M4, A1 to A4, SO1 to SO4 (With M1 to M4, A1 to A4, and SO1 to SO4 in output mode)			0.4	V
Segment driver output impedance						
[When Set Up as CMOS Output Po	rts]					
High-level output voltage	V <sub>OH</sub> 3	$V_{DD} = 2.4$ V, $I_{OH} = -10$ µA, Segment 1 to 42	V <sub>DD</sub> – 1			V
Low-level output voltage	V <sub>OL</sub> 3	$V_{DD} = 2.4 \text{ V}, I_{OL} = 40 \mu\text{A}$			1	V
High-level output voltage	V <sub>OH</sub> 4	$V_{DD}$ = 2.4 V, $I_{OH}$ = -5 $\mu$ A, Segment 1 to 42	V <sub>DD</sub> – 1			V
Low-level output voltage	V <sub>OL</sub> 4	V <sub>DD</sub> = 2.4 V, I <sub>OL</sub> = 20 µA			1	V
[When Set Up as P-Channel Open-	Drain Output	Ports]				
High-level output voltage	V <sub>OH</sub> 3	$V_{DD} = 2.4 \text{ V}, I_{OH} = -10 \ \mu\text{A}$ , Segment 1 to 42	V <sub>DD</sub> - 0.2	0.3	1	V
Output off leakage current	I <sub>OFF</sub>	$V_{DD}$ = 2.6 V, $V_{OL}$ = $V_{SS}$			1	μA
[Static Drive]						
High-level output voltage	V <sub>OH</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 µA, SEGOUT	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 6	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -4 μA, COM1	V <sub>DD</sub> – 0.2			V
Low-level output voltage	V <sub>OL</sub> 6	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 4 μA, COM1			0.2	V
[Duplex Drive (1/2 bias - 1/2 duty)]						
High-level output voltage	V <sub>OH</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 µA, SEGOUT	V <sub>DD</sub> 2-0.2			V
Low-level output voltage	V <sub>OL</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 6	$V_{DD}$ = 3.0 V, $I_{OH}$ = -4 $\mu$ A, COM1 to COM2	V <sub>DD</sub> 1 – 0.2			V
Middle-level output voltage	V <sub>OM</sub>	$V_{DD} = 3.0 \text{ V} \text{ I}_{OH} = -4 \mu\text{A}, \text{ I}_{OL} = 4 \mu\text{A}, \text{ COM1 to COM2}$			V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 6	$V_{DD} = 3.0 \text{ V}, I_{OL} = 4 \mu \text{A}, \text{COM1 to COM2}$			0.2	V
[1/2 Bias - 1/3 Duty and 1/2 Bias - 1	/4 Duty Drive	)			1 1	
High-level output voltage	V <sub>OH</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 µA, SEGOUT	V <sub>DD</sub> - 0.2			V
Low-level output voltage	V <sub>OL</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 6		V <sub>DD</sub> 2 – 0.2			V
Middle-level output voltage	V <sub>OM</sub>	$V_{DD} = 3.0 \text{ V } I_{OH} = -4 \mu A, I_{OL} = 4 \mu A,$ COM1 to COM3 (1/3 duty) COM1 to COM4 (1/4 duty)	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 6	$V_{DD} = 3.0 \text{ V}, I_{OL} = 4 \mu\text{A},$ COM1 to COM3 (1/3 duty) COM1 to COM4 (1/4 duty)			0.2	V

Parameter	Symbol	Conditions and applicable pins		Ratings		Unit
Falameter	Symbol		min	typ	max	Unit
[1/3 Bias - 1/3 Duty and 1/3 Bias - 1/	/4 Duty Drive	e]				
High-level output voltage	V <sub>OH</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OH</sub> = -0.4 μA, SEGOUT	V <sub>DD</sub> 3 + 0.2			V
Middle level output voltage	V <sub>OM</sub> 1–5	$V_{DD}$ = 3.0 V, $I_{OH}$ = –0.4 $\mu\text{A},I_{OL}$ = 0.4 $\mu\text{A},\text{SEGOUT}$	V <sub>DD</sub> 2 – 0.2		V <sub>DD</sub> 2 + 0.2	V
Middle-level output voltage	V <sub>OM</sub> 2–5	$V_{DD}$ = 3.0 V, $I_{OH}$ = –0.4 $\mu\text{A},I_{OL}$ = 0.4 $\mu\text{A},\text{SEGOUT}$	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 5	V <sub>DD</sub> = 3.0 V, I <sub>OL</sub> = 0.4 μA, SEGOUT			0.2	V
High-level output voltage	V <sub>OH</sub> 6	$ \begin{array}{l} V_{DD}=3.0 \text{ V}, \text{ I}_{OH}=-0.4 \ \mu\text{A}, \\ \text{COM1 to COM3 (in 1/3 duty mode)} \\ \text{COM1 to COM4 (in 1/4 duty mode)} \end{array} $	V <sub>DD</sub> 3 + 0.2			V
	V <sub>OM</sub> 1–6	$\label{eq:VDD} \begin{array}{l} V_{DD}=3.0 \text{ V}, \text{ I}_{OH}=-0.4 \ \mu\text{A}, \text{ I}_{OL}=0.4 \ \mu\text{A}, \\ \text{COM1 to COM3 (in 1/3 duty mode)} \\ \text{COM1 to COM4 (in 1/4 duty mode)} \end{array}$	V <sub>DD</sub> 2 – 0.2		V <sub>DD</sub> 2 + 0.2	V
Middle-level output voltage	V <sub>OM</sub> 2–6	$\label{eq:VDD} \begin{array}{l} V_{DD}=3.0 \text{ V}, \text{ I}_{OH}=-0.4 \ \mu\text{A}, \text{ I}_{OL}=0.4 \ \mu\text{A}, \\ \text{COM1 to COM3 (in 1/3 duty mode)} \\ \text{COM1 to COM4 (in 1/4 duty mode)} \end{array}$	V <sub>DD</sub> 1 – 0.2		V <sub>DD</sub> 1 + 0.2	V
Low-level output voltage	V <sub>OL</sub> 6	$V_{DD} = 3.0 \text{ V}, \text{ I}_{OL} = 0.4 \mu\text{A}$			0.2	V
[Output Voltage]						
LCD drive method: 1/3 bias						
(halver)	V <sub>DD</sub> 1	$V_{DD}$ = 3.0 V, fopg = 32.768 kHz, C1 to C4 = 0.1 µF, Figure 6	1.35			V
(tripler)	V <sub>DD</sub> 3	$V_{DD}$ = 3.0 V, fopg = 32.768 kHz, C1 to C4 = 0.1 µF, Figure 6	4.1			V
LCD drive method: 1/2 bias		-	11			
(halver)	V <sub>DD</sub> 1	V <sub>DD</sub> = 3.0 V, fopg 32.768 kHz, C1 = C2 = 0.1 µF, Figure 7	1.35			V
[Current Drain (With the backup flag	cleared)]		11			
LCD drive method: 1/3 bias	I <sub>DD</sub>	$V_{DD}$ = 3.0 V, Halt mode, C1 to C4 = 0.1 µF, Cl = 25 kΩ Co = Cg = 20 pF, 32.768 kHz Xtal, Figure 6		5.0		μA
LCD drive methods other than 1/3 bias	I <sub>DD</sub>	$V_{DD}$ = 3.0 V, Halt mode, C1 to C2 = 0.1 $\mu$ F, Cl = 25 k $\Omega$ , Figure 7, Co = Cg = 20 pF, 32.768 kHz, Xtal		5.0		μA
Oscillator start voltage	Vstt	$V_{DD} = V_{DD}^2$ , CI = 25 k $\Omega$ , Figure 4, Co = Cg = 20 pF, 32.768 kHz Xtal			2.2	V
Oscillator hold voltage (with the backup flag cleared)	V <sub>HOLD</sub>	$V_{DD}$ = $V_{DD}$ 2, CI = 25 k $\Omega$ , , Figures 5, 6, 7, and 8, Co = Cg = 20 pF, 32.768 kHz Xtal	2.0			V
Oscillator start time	Tstt	$V_{DD} = V_{DD}2 = 2.2 \text{ V}, \text{ CI} = 25 \text{ k}\Omega, \text{ Figure 4}$ Co = Cg = 20 pF, 32.768 kHz Xtal			10	sec
Oscillator correction capacitance	10P	XC	8	10	12	pF
Oscillator correction capacitance	20P	ХТОИТ	16	20	24	pF

Note : 1. S1 to 4, K1 to 4 2. M1 to 4, A1 to 4, SO1 to 4

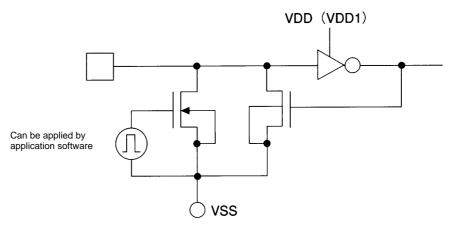


Figure 1 S1 to S4, K1 to K4, M1 to M4, A1 to A4, and SO1 to SO4

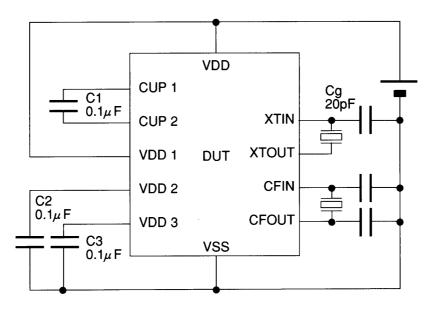


Figure 2 Output Voltage, Current Drain, and Oscillator Hold Voltage Test Circuit

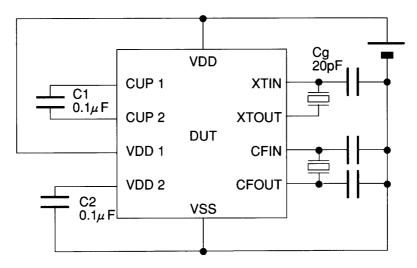


Figure 3 Output Voltage, Current Drain, and Oscillator Hold Voltage Test Circuit

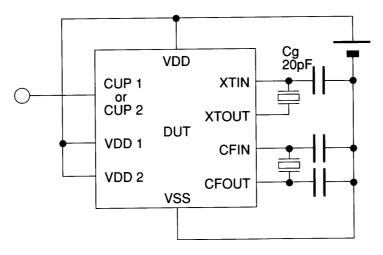


Figure 4 Oscillator Start Voltage, Oscillator Start Time, and Frequency Stability Test Circuit

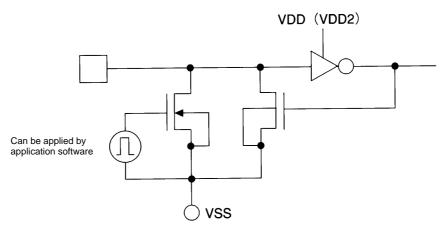


Figure 5 S1 to S4, K1 to K4, M1 to M4, A1 to A4, and SO1 to SO4

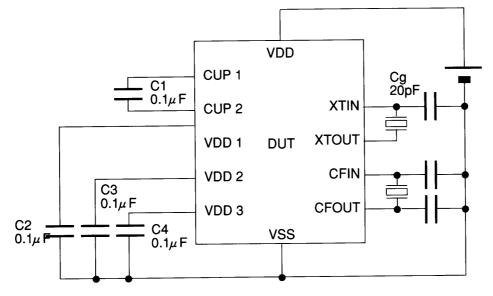


Figure 6 Output Voltage, Current Drain, and Oscillator Hold Voltage Test Circuit

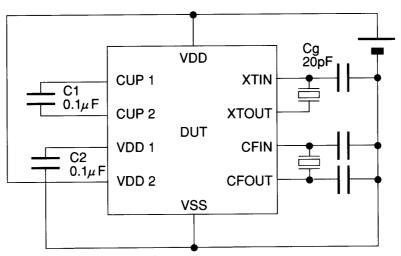
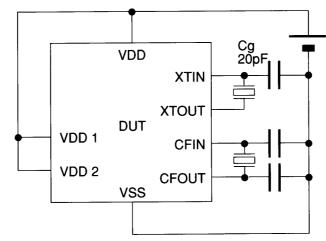


Figure 7 Output Voltage, Current Drain, and Oscillator Hold Voltage Test Circuit



#### Figure 8 Output Voltage, Current Drain, and Oscillator Hold Voltage Test Circuit

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